

## AMENDMENTS TO THE CLAIMS

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1-92. (Canceled)

Σ 1  
93. (New) A planar conductive material structure usable in manufacturing an interconnect for an integrated circuit comprising:

a substrate having a top portion that includes a surface portion and a cavity portion, wherein the cavity portion has at least a first cavity and a second cavity; and

a planar conductive layer that is formed within the cavity portion and on the surface portion such that a predetermined thickness range of the planar conductive layer over the surface portion is between one tenth and one half of the thickness of the planar conductive layer within the cavity portion.

94. (New) The structure of Claim 93, wherein the first cavity has a width less than one micron, and the second cavity has a width larger than 10 microns.

95. (New) The structure of Claim 93, wherein the top portion includes an insulator layer and a barrier layer overlying said insulator layer and wherein the cavities are formed in the insulator layer.

96. (New) The structure of Claim 93, wherein the planar conductive layer comprises copper or copper alloy.

97. (New) A conductive bead structure usable in manufacturing an interconnect for an integrated circuit comprising:

a substrate having a top portion that includes a surface portion and a cavity portion, wherein the cavity portion has at least a first cavity having a submicron width and a second cavity having a width larger than 10 microns; and

conductive beads formed within each cavity, wherein each conductive bead protrudes above a level of the surface portion of the substrate and is confined within a respective cavity.

98. (New) The structure of Claim 97, wherein the top portion includes an insulator layer and a barrier layer overlying said insulator layer, and wherein the cavities are formed in the insulator layer.

99. (New) The structure of Claim 97, wherein the planar conductive material comprises copper or copper alloy.

Σ 1

